



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

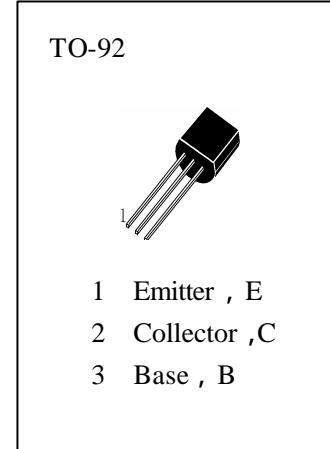
**H1426**

## APPLICATIONS

DC-DC Convertor

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$ —Storage Temperature.....	-55~150
$T_j$ —Junction Temperature.....	150
$P_c$ —Collector Dissipation.....	750mW
$V_{CBO}$ —Collector-Base Voltage.....	-20V
$V_{CEO}$ —Collector-Emitter Voltage.....	-20V
$V_{EBO}$ —Emitter-Base Voltage.....	-6V
$I_c$ —Collector Current.....	-3 A
$I_b$ —Base Current.....	-200mA



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{CBO}$	Collector-Base Breakdown Voltage	-20			V	$I_C=-50 \mu A, I_E=0$
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	-20			V	$I_C=-1mA, I_B=0$
$BV_{EBO}$	Emitter-Base Breakdown Voltage	-6			V	$I_E=-10 \mu A, I_C=0$
$I_{CBO}$	Collector Cut-off Current			-0.1	$\mu A$	$V_{CB}=-20V, I_E=0$
$I_{EBO}$	Emitter Cut-off Current			-0.1	$\mu A$	$V_{EB}=-5V, I_C=0$
$H_{FE}$	DC Current Gain	82		390		$V_{CE}=-2V, I_C=-100mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-0.5	V	$I_C=-2A, I_B=-100mA$
$f_T$	Current Gain- Bandwidth Product		240		MHz	$V_{CE}=-2V, I_C=-500mA, f=100MHz$
$C_{ob}$	Output Capacitance		35		pF	$V_{CB}=-10V, I_E=0, f=1MHz$

### $h_{FE}$ Classification

**P****Q****R**

82—180

120—270

180—390